MC10EP16VA, MC100EP16VA

3.3 V / 5 V ECL Differential Receiver/Driver with High Gain

ON Semiconductor®

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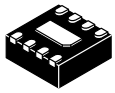
SOIC−8 NB
D SUFFIX
CASE 751−07

TSSOP−8
DT SUFFIX
CASE 948R−02



DFN8
MN SUFFIX
CASE 506AA

Description

The EP16VA is a world-class differential receiver/driver. The device is functionally equivalent to the EP16 and LVEP16 devices but with high gain output. Q_{HG} and $\overline{Q_{HG}}$ outputs have a DC gain several times larger than the DC gain of an EP16.

The V_{BB} pin, an internally generated voltage supply, is available to this device only. For single-ended input conditions, the unused differential input is connected to V_{BB} as a switching reference voltage. V_{BB} may also rebias AC coupled inputs. When used, decouple V_{BB} and V_{CC} via a 0.01 μF capacitor and limit current sourcing or sinking to 0.5 mA. When not used, V_{BB} should be left open.

Under open input conditions (pulled to V_{EE}) internal input clamps will force the Q_{HG} output LOW.

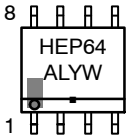
Special considerations are required for differential inputs under No Signal conditions to prevent instability.

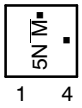
The 100 Series contains temperature compensation.

Features

- 270 ps Typical Propagation Delay
- Gain = > 20
- 20 mV Minimum Input Voltage Swing
- Maximum Frequency = > 3 GHz Typical
- PECL Mode Operating Range:
  V_{CC} = 3.0 V to 5.5 Vwith V_{EE} = 0 V
- NECL Mode Operating Range:
  V_{CC} = 0 V with V_{EE} = −3.0 V to −5.5 V
- Open Input Default State
- V_{BB} Output
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

MARKING DIAGRAMS*

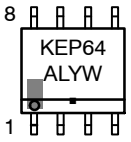


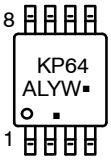


SOIC−8 NB

TSSOP−8

DFN8





H	= MC10	A	= Assembly Location
K	= MC100	L	= Wafer Lot
5M	= MC10	Y	= Year
3D	= MC100	W	= Work Week
M	= Date Code	▪	= Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

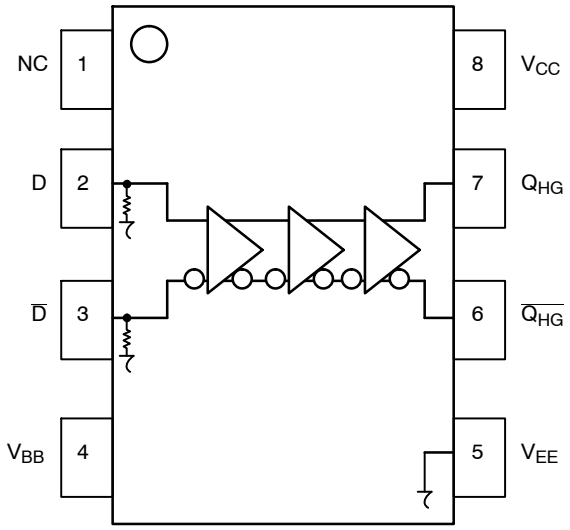


Figure 1. 8-Lead Pinout (Top View) **and Logic Diagram**

Table 1. PIN DESCRIPTION

PIN	FUNCTION
D*, $\overline{D}$*	ECL Data Inputs
Q_{HG}, $\overline{Q_{HG}}$	ECL High Gain Data Outputs
V_{BB}	Reference Voltage Output
V_{CC}	Positive Supply
V_{EE}	Negative Supply
NC	No Connect
EP	(DFN8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

* Pins will default LOW when left open.

Table 2. ATTRIBUTES

Characteristics		Value
Internal Input Pulldown Resistor		75 kΩ
Internal Input Pullup Resistor		N/A
ESD Protection Human Body Model Machine Model Charged Device Model		 > 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)		Pb-Free Pkg
SOIC−8 NB TSSOP−8 DFN8		Level 1 Level 3 Level 1
Flammability Rating	Oxygen Index: 28 to 34	UL−94 V−0 @ 0.125 in
Transistor Count		167
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test		

1. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	PECL Mode Power Supply	V_{EE} = 0 V		6	V
V_{EE}	NECL Mode Power Supply	V_{CC} = 0 V		−6	V
V_I	PECL Mode Input Voltage NECL Mode Input Voltage	V_{EE} = 0 V V_{CC} = 0 V	$V_I \le V_{CC}$ $V_I \ge V_{EE}$	6 −6	V
I_{out}	Output Current	Continuous Surge		50 100	mA
I_{BB}	V_{BB} Sink/Source			±0.5	mA
T_A	Operating Temperature Range			−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC−8 NB SOIC−8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC−8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP−8 TSSOP−8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP−8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN8 DFN8	129 84	°C/W
T_{sol}	Wave Solder (Pb-Free)	< 2 to 3 sec @ 260°C		265	°C
θ_{JC}	Thermal Resistance (Junction-to-Case)	(Note 2)	DFN8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. JEDEC standard multilayer board − 2S2P (2 signal, 2 power)

Table 4. 10EP DC CHARACTERISTICS, PECL (V_{CC} = 3.3 V, V_{EE} = 0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	20	28	36	22	30	38	24	32	40	mA
V_{OH}	Output HIGH Voltage (Note 2)	2165	2240	2415	2230	2355	2480	2290	2415	2540	mV
V_{OL}	Output LOW Voltage (Note 2)	1365	1490	1615	1430	1555	1680	1490	1615	1740	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	2090		2415	2155		2480	2215		2540	mV
V_{IL}	Input LOW Voltage (Single-Ended)	1365		1690	1460		1755	1490		1815	mV
V_{BB}	Output Voltage Reference	1790	1950	1990	1855	2000	2055	1915	2040	2115	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		3.3	2.0		3.3	2.0		3.3	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.3 V to −2.2 V.
2. All loading with 50 Ω to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 5. 10EP DC CHARACTERISTICS, PECL (V_{CC} = 5.0 V, V_{EE} = 0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	20	28	36	22	30	38	24	32	40	mA
V_{OH}	Output HIGH Voltage (Note 2)	3865	3940	4115	3930	4055	4180	3990	4115	4240	mV
V_{OL}	Output LOW Voltage (Note 2)	3065	3190	3315	3130	3255	3380	3190	3315	3440	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	3790		4115	3855		4180	3915		4240	mV
V_{IL}	Input LOW Voltage (Single-Ended)	3065		3390	3130		3455	3190		3515	mV
V_{BB}	Output Voltage Reference	3490	3633	3690	3555	3670	3755	3615	3710	3815	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		5.0	2.0		5.0	2.0		5.0	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +2.0 V to −0.5 V.
2. All loading with 50 Ω to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 6. 10EP DC CHARACTERISTICS, NECL (V_{CC} = 0 V; V_{EE} = −5.5 V to −3.0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	20	28	36	22	30	38	24	32	40	mA
V_{OH}	Output HIGH Voltage (Note 2)	−1135	−1060	−885	−1070	−945	−820	−1010	−885	−760	mV
V_{OL}	Output LOW Voltage (Note 2)	−1935	−1810	−1685	−1870	−1745	−1620	−1810	−1685	−1560	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	−1210		−885	−1145		−820	−1085		−760	mV
V_{IL}	Input LOW Voltage (Single-Ended)	−1935		−1610	−1870		−1545	−1810		−1485	mV
V_{BB}	Output Voltage Reference	−1510	−1367	−1310	−1445	−1330	−1245	−1385	−1290	−1185	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	V_{EE}+2.0		0.0	V_{EE}+2.0		0.0	V_{EE}+2.0		0.0	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}.
2. All loading with 50 Ω to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 7. 100EP DC CHARACTERISTICS, PECL (V_{CC} = 3.3 V, V_{EE} = 0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	22	28	36	24	30	40	26	32	42	mA
V_{OH}	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V_{OL}	Output LOW Voltage (Note 2)	1305	1430	1555	1305	1430	1555	1305	1430	1555	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	2075		2420	2075		2420	2075		2420	mV
V_{IL}	Input LOW Voltage (Single-Ended)	1355		1675	1355		1675	1355		1675	mV
V_{BB}	Output Voltage Reference	1775	1875	1975	1775	1875	1975	1775	1875	1975	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		3.3	2.0		3.3	2.0		3.3	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.3 V to −2.2 V.
2. All loading with 50 Ω to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 8. 100EP DC CHARACTERISTICS, PECL (V_{CC} = 5.0 V, V_{EE} = 0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	22	28	36	24	30	40	26	32	42	mA
V_{OH}	Output HIGH Voltage (Note 2)	3855	3980	4105	3855	3980	4105	3855	3980	4105	mV
V_{OL}	Output LOW Voltage (Note 2)	3005	3180	3355	3005	3180	3355	3005	3180	3355	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	3775		4120	3775		4120	3775		4120	mV
V_{IL}	Input LOW Voltage (Single-Ended)	3055		3375	3055		3375	3055		3375	mV
V_{BB}	Output Voltage Reference	3475	3575	3675	3475	3575	3675	3475	3575	3675	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.0		5.0	2.0		5.0	2.0		5.0	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +2.0 V to −0.5 V.
2. All loading with 50 Ω to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 9. 100EP DC CHARACTERISTICS, NECL (V_{CC} = 0 V; V_{EE} = −5.5 V to −3.0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current	22	28	36	24	30	40	26	32	42	mA
V_{OH}	Output HIGH Voltage (Note 2)	−1145	−1020	−895	−1145	−1020	−895	−1145	−1020	−895	mV
V_{OL}	Output LOW Voltage (Note 2)	−1995	−1870	−1745	−1995	−1870	−1745	−1995	−1870	−1745	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	−1225		−880	−1225		−880	−1225		−880	mV
V_{IL}	Input LOW Voltage (Single-Ended)	−1945		−1625	−1945		−1625	−1945		−1625	mV
V_{BB}	Output Voltage Reference	−1525	−1425	−1325	−1525	−1425	−1325	−1525	−1425	−1325	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	V_{EE}+2.0		0.0	V_{EE}+2.0		0.0	V_{EE}+2.0		0.0	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}.
2. All loading with 50 Ω to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 10. AC CHARACTERISTICS (V_{CC} = 0 V; V_{EE} = −3.0 V to −5.5 V or V_{CC} = 3.0 V to 5.5 V; V_{EE} = 0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{max}	Maximum Frequency (See Figure 2 F_{max}/JITTER)		> 3			> 3			> 3		GHz
t_{PLH}, t_{PHL}	Propagation Delay to Output Differential	200	260	320	220	270	340	250	320	390	ps
t_{SKEW}	Duty Cycle Skew (Note 2)		5.0	20		5.0	20		5.0	20	ps
t_{JITTER}	Cycle-to-Cycle Jitter (See Figure 2 F_{max}/JITTER)		0.2	< 1		0.2	< 1		0.2	< 1	ps
V_{PP}	Input Voltage Swing (Differential Configuration) (See Figure 3)	20	800	1200	20	800	1200	20	800	1200	mV
t_r t_f	Output Rise/Fall Times Q, $\overline{Q}$ (20% − 80%)	70	110	170	80	110	180	80	120	200	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Measured using a 750 mV source, 50% duty cycle clock source. All loading with 50 Ω to V_{CC}−2.0 V.
2. Skew is measured between outputs under identical transitions. Duty cycle skew is defined only for differential operation when the delays are measured from the cross point of the inputs to the cross point of the outputs.

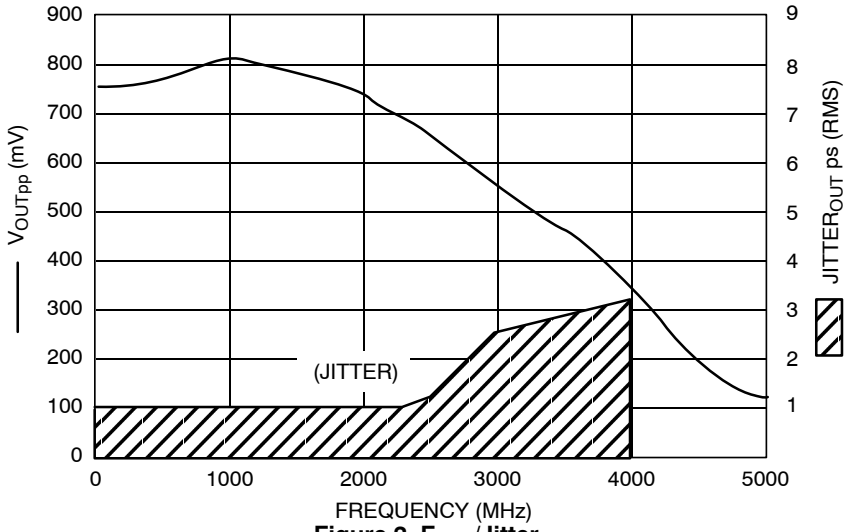


Figure 2. F_{max}/Jitter

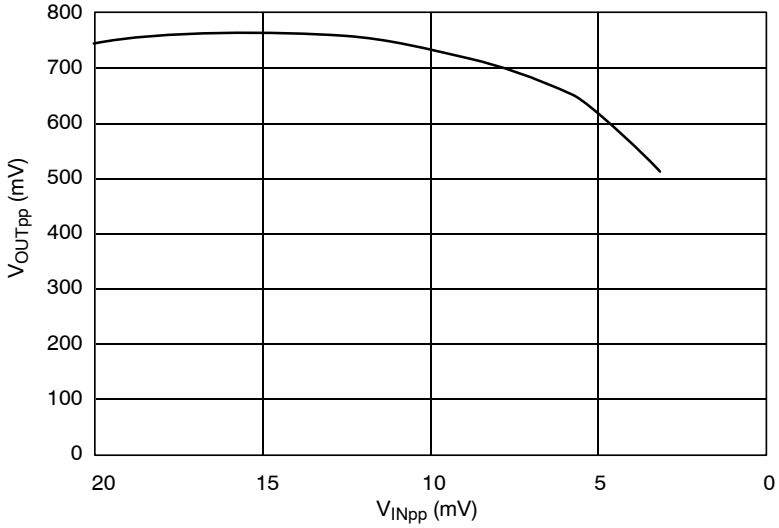


Figure 3. Gain vs. Input Voltage (50 MHz)

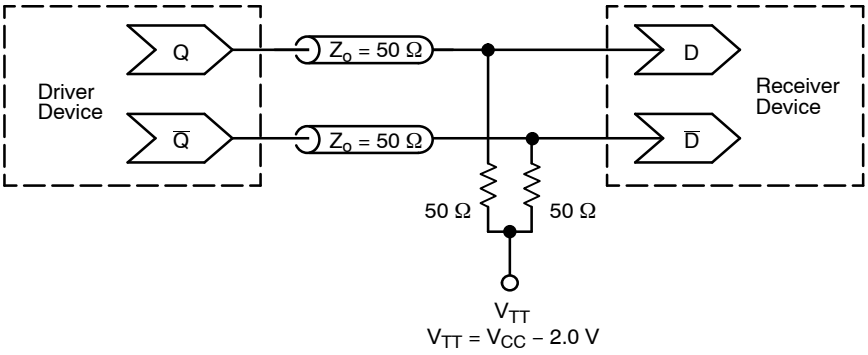


Figure 4. Typical Termination for Output Driver and Device Evaluation
(See Application Note AND8020/D – Termination of ECL Logic Devices)

ORDERING INFORMATION

Device	Package	Shipping†
MC10EP16VADG	SOIC−8 NB (Pb-Free)	98 Units / Rail
MC10EP16VADR2G	SOIC−8 NB (Pb-Free)	2500 / Tape & Reel
MC10EP16VADTG	TSSOP−8 (Pb-Free)	100 Units / Rail
MC10EP16VADTR2G	TSSOP−8 (Pb-Free)	2500 / Tape & Reel
MC10EP16VAMNR4G	DFN8 (Pb-Free)	1000 / Tape & Reel
MC100EP16VADG	SOIC−8 NB (Pb-Free)	98 Units / Rail
MC100EP16VADR2G	SOIC−8 NB (Pb-Free)	2500 / Tape & Reel
MC100EP16VADTG	TSSOP−8 (Pb-Free)	100 Units / Rail
MC100EP16VADTR2G	TSSOP−8 (Pb-Free)	2500 / Tape & Reel
MC100EP16VAMNR4G	DFN8 (Pb-Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Resource Reference of Application Notes

AN1405/D – ECL Clock Distribution Techniques

AN1406/D – Designing with PECL (ECL at +5.0 V)

AN1503/D – ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D – Metastability and the ECLinPS Family

AN1568/D – Interfacing Between LVDS and ECL

AN1672/D – The ECL Translator Guide

AND8001/D – Odd Number Counters Design

AND8002/D – Marking and Date Codes

AND8020/D – Termination of ECL Logic Devices

AND8066/D – Interfacing with ECLinPS

AND8090/D – AC Characteristics of ECL Devices

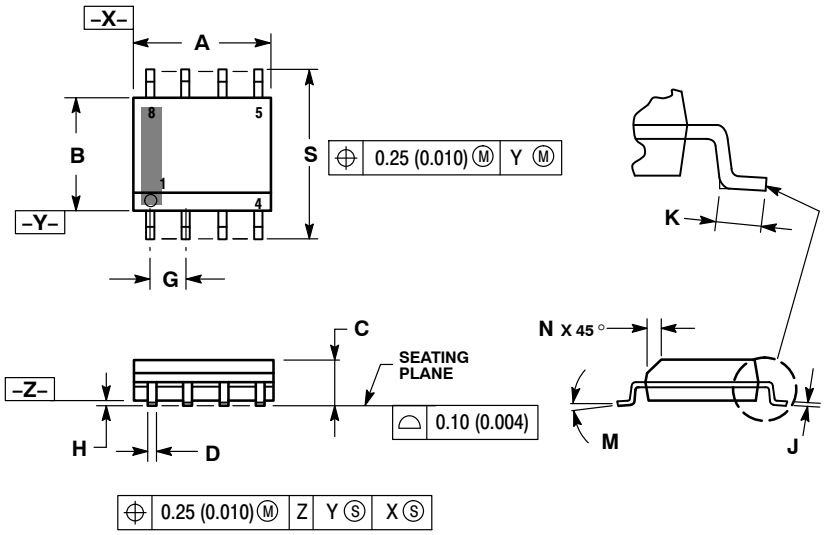
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

SCALE 1:1

SOIC−8 NB
CASE 751−07
ISSUE AK

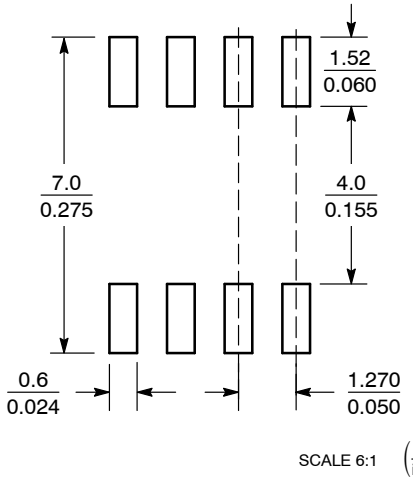
DATE 16 FEB 2011



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

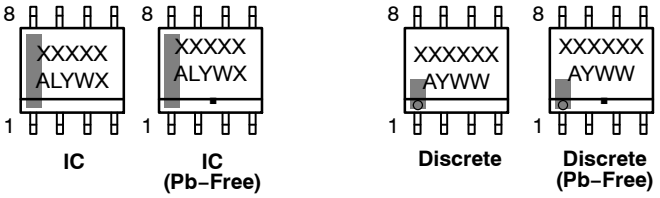
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42564B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**SOIC−8 NB**		**PAGE 1 OF 2**

SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. BASE, #2
6. EMITTER, #2
7. BASE, #1
8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. GATE, #2
6. SOURCE, #2
7. GATE, #1
8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
7. ANODE
8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. DRAIN
5. GATE
6. GATE
7. SOURCE
8. SOURCE

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. DRAIN
4. SOURCE
5. SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 7:
PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
2. BASE, #1
3. BASE, #2
4. COLLECTOR, #2
5. COLLECTOR, #2
6. EMITTER, #2
7. EMITTER, #1
8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
2. COLLECTOR, DIE #1
3. COLLECTOR, DIE #2
4. EMITTER, COMMON
5. EMITTER, COMMON
6. BASE, DIE #2
7. BASE, DIE #1
8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND
5. GROUND
6. BIAS 2
7. INPUT
8. GROUND

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
2. N−GATE
3. P−SOURCE
4. P−GATE
5. P−DRAIN
6. P−DRAIN
7. N−DRAIN
8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
2. V2OUT
3. V1OUT
4. TXE
5. RXE
6. VEE
7. GND
8. ACC

STYLE 18:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3
4. CATHODE 4
5. CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
2. N/C
3. REXT
4. GND
5. IOUT
6. IOUT
7. IOUT
8. IOUT

STYLE 26:
PIN 1. GND
2. dv/dt
3. ENABLE
4. ILIMIT
5. SOURCE
6. SOURCE
7. SOURCE
8. VCC

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
2. DASIC_OFF
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
2. EMITTER, #1
3. BASE, #2
4. EMITTER, #2
5. COLLECTOR, #2
6. COLLECTOR, #2
7. COLLECTOR, #1
8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
6. SOURCE 1/DRAIN 2
7. SOURCE 1/DRAIN 2
8. GATE 1

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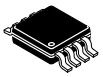
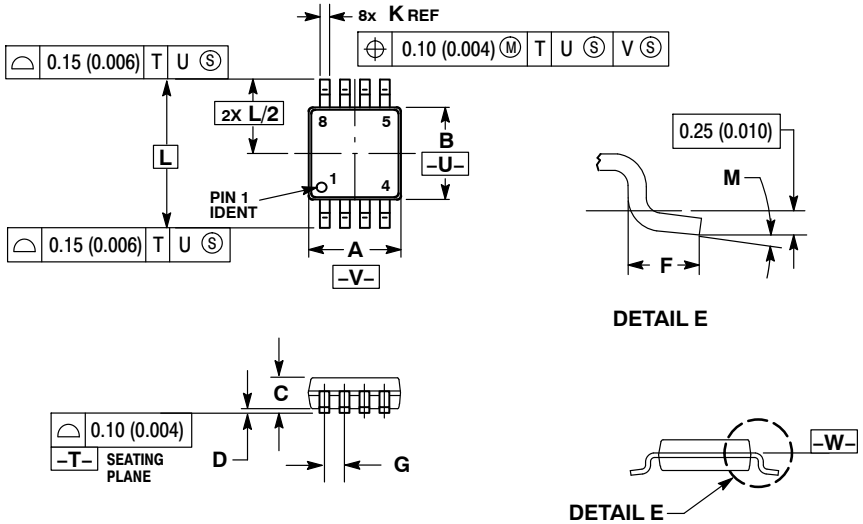
DESCRIPTION:	**SOIC−8 NB**		**PAGE 2 OF 2**

TSSOP 8
CASE 948R–02
ISSUE A

DATE 04/07/2000



SCALE 2:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	0°	6°	0°	6°

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